

SSCN5551GSG

High Frequency High Gain NPN Power BJT

Features

VCB	VCE	VEB	IC
180V	160V	6V	200mA

Description

This device is designed for general-purpose high-voltage amplifiers and gas discharge display drivers. It is Ideal for medium power amplification and switching.

Applications

- General-purpose high-voltage amplifiers
- Gas discharge display drivers
- Medium power amplification and switching

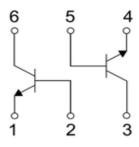
Ordering Information

Device	Package	Shipping
SSCN5551GSG	SOT-363	3000/Reel

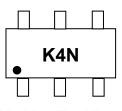
> Pin configuration



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Circuit Diagram



Marking(Top View)



SSCN5551GSG

➤ Absolute Maximum Ratings(T_A=25°C unless otherwise noted)

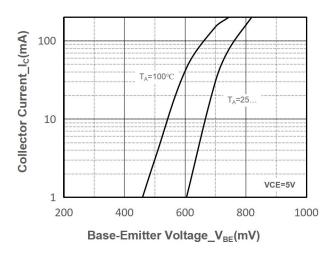
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	180	V
Collector- Emitter Voltage	V _{CEO}	160	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current-Continuous	Ic	200	mA
Collector Power Dissipation	Pc	200	mW
Junction Temperature	TJ	-55 to 150	$^{\circ}$
Storage Temperature	T _{STG}	-55 to 150	$^{\circ}$

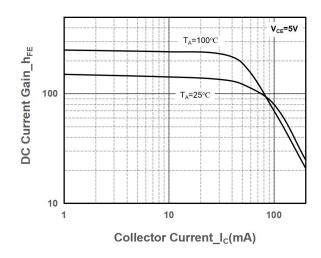
➤ Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =0.1mA, I _E =0	180			V	
Collector-emitter Breakdown Voltage	BV _{CEO}	I _C =1mA, I _B =0	160			V	
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E =0.1mA, I _C =0	6			V	
Collector Cutoff Current	I _{CBO}	V _{CB} =120V, I _E =0			0.05	μA	
Emitter Cutoff Current	I _{EBO}	V _{EB} =4V, I _C =0			0.05	μA	
	h _{FE1}	V _{CE} =5V, I _C =1mA	80				
DC Current Gain	h _{FE2}	V _{CE} =5V, I _C =10mA	100		300		
	h _{FE3}	V _{CE} =5V, I _C =50mA	30				
Collector Emitter Seturation Voltage	V _{CE} (sat)1	I _C =10mA, I _B =1mA			0.15	V	
Collector-Emitter Saturation Voltage	V _{CE (sat)2}	I _C =50mA, I _B =5mA			0.2		
Base-Emitter Saturation Voltage	V _{BE (sat)1}	I _C =10mA, I _B =1mA			1.0	0 V	
Base-Emilier Saturation voltage		I _C =50mA, I _B =5mA			1.0	V	
Output Canacitance	Cob	VCB=10V, IE=0,			6	nE	
Output Capacitance	COD	f=1MHz			6	pF	βF
Noigo Figuro	NF	VCE=5V, IC=-200uA,			8.0	dB	
Noise Figure	INF	f=1KHz, Rs=1KΩ			6.0		
Transition frequency	f⊤	V _{CE} =10V, I _C =10mA	100		300 MHz		
Transition frequency	IT IT	f=100MHz	100		300	IVII IZ	



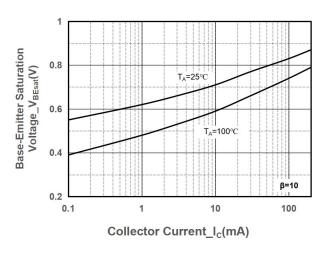
➤ Typical Performance Characteristics (T_A=25°C unless otherwise noted)

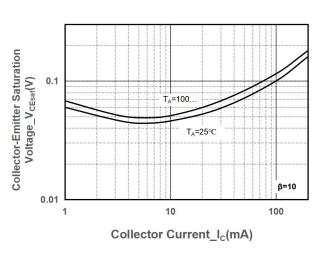




Collector Current vs. Base-Emitter Voltage

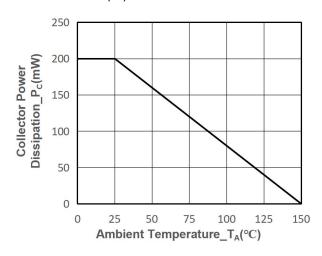
DC Current Gain vs. Collector Current

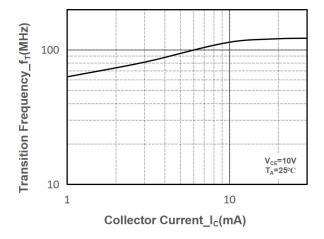




V_{BE(sat)} vs. Collector Current

V_{CE(sat)} vs. Collector Current





Power derating vs. Ambient temperature

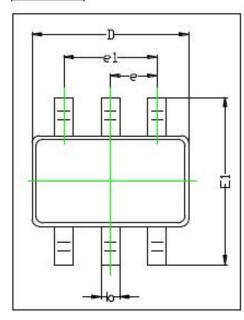
Transition Frequency vs. Collector Current



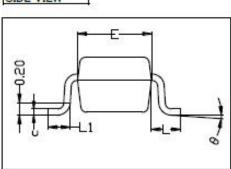
Package Information

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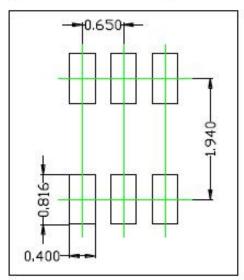
TOP VIEW



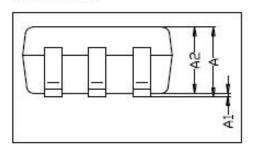
SIDE VIEW



SOLDRING PATTERN



FRONT VIEW



SYMBOL	DIMENSIONS I	N MILLIMETER
SIMBUL	MIN	MAX
Α	0.900	1.000
A1	0.000	0.100
A2	0.900	1.000
р	0.150	0.300
0	0.100	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.400
e	0.650) TYP.
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.450
Ф	0.	8°



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